



Dual N-Channel 30-V (D-S) MOSFET with Schottky Diode

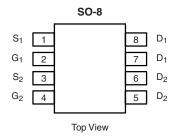
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)			
30	0.022 at V _{GS} = 10 V	7.5			
	0.030 at V _{GS} = 4.5 V	6.5			

SCHOTTKY PRODUCT SUMMARY					
V _{DS} (V)	V _{SD} (V) Diode Forward Voltage	I _F (A)			
30	0.50 V at 1.0 A	2.0			

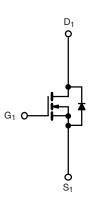
FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- LITTLE FOOT® Plus
- Compliant to RoHS directive 2002/95/EC

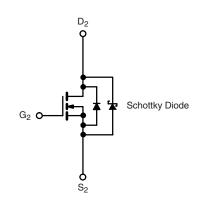




Ordering Information: Si4808DY-T1-E3 (Lead (Pb)-free) Si4808DY-T1-GE3 (Lead (Pb)-free and Halogen-free)







N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted							
Parameter	Symbol	10 s	Steady State	Unit			
Drain-Source Voltage		V_{DS}	30		V		
Gate-Source Voltage		V_{GS}	±	V			
Continuous Dunin Comment /T 450 °C\d	T _A = 25 °C	ı	7.5	5.7			
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	l _D	6.0	4.6	Δ.		
Pulsed Drain Current		I _{DM}	3	Α			
Continuous Source Current (Diode Conduction) ^a		I _S	1.7	1.7 0.9			
Marrian III Danier Disain attend	T _A = 25 °C	P _D	2.0	1.1	W		
Maximum Power Dissipation ^a	T _A = 70 °C	'D	1.3	0.7	VV		
Operating Junction and Storage Temperature Rang	T _J , T _{stg}	- 55 t	°C				

THERMAL RESISTANCE RATINGS								
			MOSFET		Schottky			
Parameter		Symbol	Тур.	Max.	Тур.	Max.	Unit	
Manigan ya kunatian ta Amahianta	t ≤ 10 s	- R _{thJA}	52	62.5	53	62.5	°C/W	
Maximum Junction-to-Ambient ^a	Steady-State		93	110	93	110		
Maximum Junction-to-Foot (Drain)	Steady-State	R_{thJC}	35	40	35	40		

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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MOSFET SPECIFICATION	NS T _J = 2	25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Typ. ^a	Max.	Unit			
Static	•				•				
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$		0.8			V		
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$				± 100	nA		
		$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	Ch-1			1			
Zero Gate Voltage Drain Current	I _{DSS}	VDS - 2+ V, VGS - 0 V	Ch-2			100	μΑ		
Zero date voltage Brain Gurrent	.022	V _{DS} = 24 V, V _{GS} = 0 V, T _J = 85 °C	Ch-1			15	μΛ		
			Ch-2			2000			
On-State Drain Current ^b	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$		20			Α		
Dunin Course On Otata Basistanash	B	$V_{GS} = 10 \text{ V}, I_D = 7.5 \text{ A}$			0.018	0.022	0		
Drain-Source On-State Resistance ^b	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 6.5 \text{ A}$			0.024	0.030	Ω		
Forward Transconductance ^b	9 _{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 7.5 \text{ A}$			22		S		
Diada Famuard Valtarah	V _{SD}	I _S = 1 A, V _{GS} = 0 V	Ch-1		0.8	1.2	V		
Diode Forward Voltage ^b	V SD	Ch-2			0.47	0.5			
Dynamic ^a									
Total Gate Charge	Q_g				13	20			
Gate-Source Charge	Q_{gs}	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 7$.5 A		2		nC		
Gate-Drain Charge	Q_{gd}				2.7				
Gate Resistance	R_g			0.5		3.2	Ω		
Turn-On Delay Time	t _{d(on)}				8	16			
Rise Time	t _r	$V_{DD} = 15 \text{ V}, R_{L} = 15 \Omega$			10	20			
Turn-Off Delay Time	t _{d(off)}	$I_D \cong 1 \text{ A, V}_{GEN} = 10 \text{ V, R}_g = 6 \Omega$			21	40	ns		
Fall Time	t _f				10	20	110		
Source-Drain Reverse Recovery	+	I _E = 1.7 A, dI/dt = 100 A/μs	Ch-1		40	80			
Time	t _{rr}	$r_F = 1.7 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{S}$ Ch-2			32	70			

Notes:

- a. Guaranteed by design, not subject to production testing. b. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

SCHOTTKY SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Forward Voltage Drop	V _F	I _F = 1.0 A		0.47	0.50	V		
		$I_F = 1.0 \text{ A}, T_J = 125 ^{\circ}\text{C}$		0.36	0.42			
Maximum Reverse Leakage Current	I _{rm}	V _R = 30 V		0.004	0.100	mA		
		V _R = 30 V, T _J = 100 °C		0.7	10			
		V _R = - 30 V, T _J = 125 °C		3.0	20			
Junction Capacitance	C _T	V _R = 10 V		50		pF		

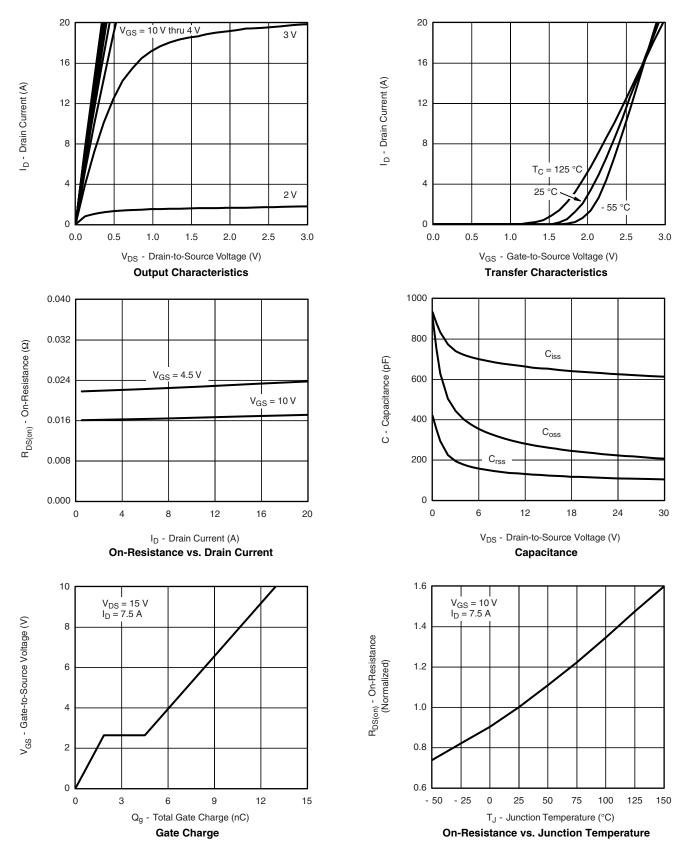
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.







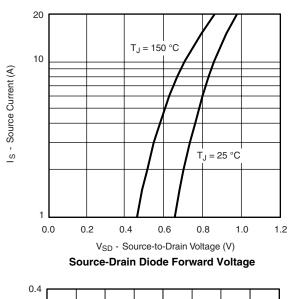
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

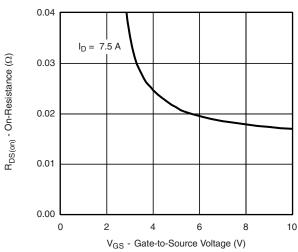


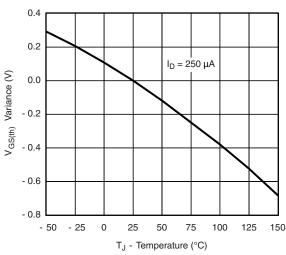
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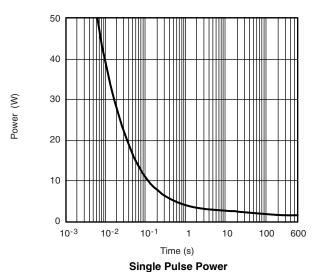
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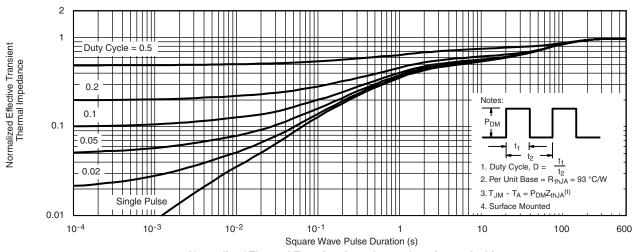




On-Resistance vs. Gate-to-Source Voltage



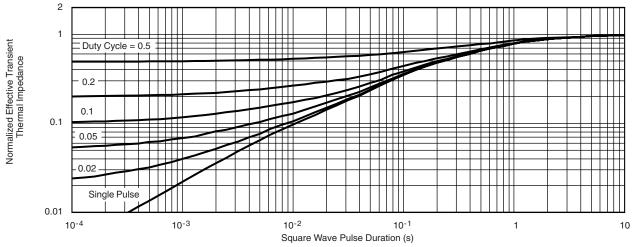
Threshold Voltage



Normalized Thermal Transient Impedance, Junction-to-Ambient

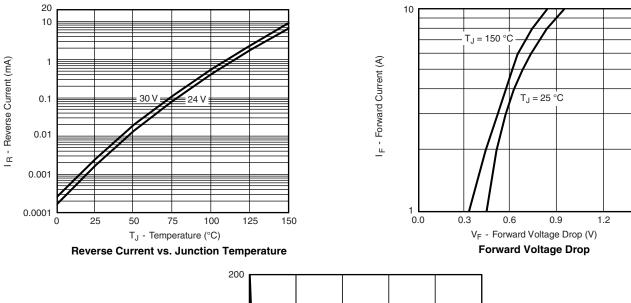


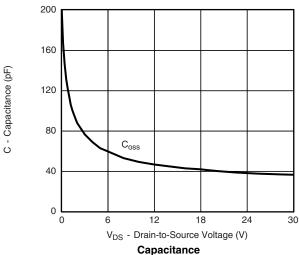
MOSFET TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Foot

SCHOTTKY TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





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